AS4407CS-Q1

P-Channel Enhancement Mode MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-30V	10mΩ@-20V	-12A
	12mΩ@-10V	
	15mΩ@-6V	
	20mΩ@-4.5V	

Feature

- Trench Power LV MOSFET technology
- High density cell design for low $R_{DS(ON)}$
- High Speed switching
- Suffix "-Q1" for AEC-Q101

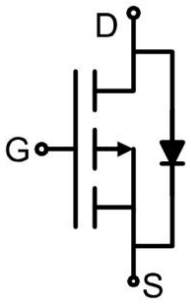
Application

- Battery protection
- Load switch
- Power management

Package

SOP-8

Circuit diagram



Marking

AS4407CS-Q1

P-Channel Enhancement Mode MOSFET

Absolute maximum ratings (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±25	V
Continuous Drain Current	I_D	-12	A
Continuous Drain Current(T_A=100℃)	I_D(100℃)	-7.5	A
Pulsed Drain Current[1)]	I_{DM}	-100	A
Avalanche energy[2)]	E_{AS}	100	mJ
Power Dissipation[3)]	P_D	2.5	W
Thermal Resistance,Junction-to-Ambient[4)]	$R_{\theta JA}$	50	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55 ~ +150	℃

Electrical characteristics (T_J=25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} =0V, I_D =-250μA	-30			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =-30V,V_{GS} =0V			-1	μA
Gate-body leakage current	I_{GSS}	V_{GS} =±25V, V_{DS} =0V			±100	nA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =-250μA	-1.2	-1.8	-2.8	V
Drain-source on-resistance	$R_{DS(on)}$	V_{GS} =-20V, I_D =-12A		7.5	10	mΩ
		V_{GS} =-10V, I_D =-12A		9	12	
		V_{GS} =-6V, I_D =-10A		11	15	
		V_{GS} =-4.5V, I_D =-10A		14.5	20	
Dynamic characteristics[5)]						
Input Capacitance	C_{iss}	V_{DS} =-15V,V_{GS} =0V,f =1MHz		1860		pF
Output Capacitance	C_{oss}			310		
Reverse Transfer Capacitance	C_{rss}			280		
Total Gate Charge	Q_g	V_{DS} =-15V,V_{GS} =-10V,I_D =-12A		38		nC
Gate-Source Charge	Q_{gs}			5		
Gate-Drain Charge	Q_{gd}			10		
Turn-on delay time	$t_{d(on)}$	V_{DD} =-15V,V_{GS} =-10V, I_D =-12A,R_{GEN} =2.3Ω		8		nS
Turn-on rise time	t_r			6		
Turn-off delay time	$t_{d(off)}$			95		
Turn-off fall time	t_f			62		
Source-Drain Diode characteristics						
Diode Forward Current	I_S				-12	A
Diode Forward voltage	V_{SD}	V_{GS} =0V, I_S=-12A			-1.2	V
Reverse Recovery Time	t_{rr}	I_F=-12A, di/dt=100A/us		40		nS
Reverse Recovery Charge	Q_{rr}			19		nC

Notes:

1) Repetitive rating; pulse width limited by max. junction temperature.

2) T_J=25℃, V_{DD}=-20V, V_G=-10V, R_G=25Ω, L=0.5mH, I_{AS}=-20A.

3) P_d is based on max. junction temperature, using junction-case and junction-ambient thermal resistance.

4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in the still air environment with T_A =25℃. The maximum allowed junction temperature of 150℃. The value in any given application depends on the user's specific board design.

5) Guaranteed by design, not subject to production.

Typical Characteristics

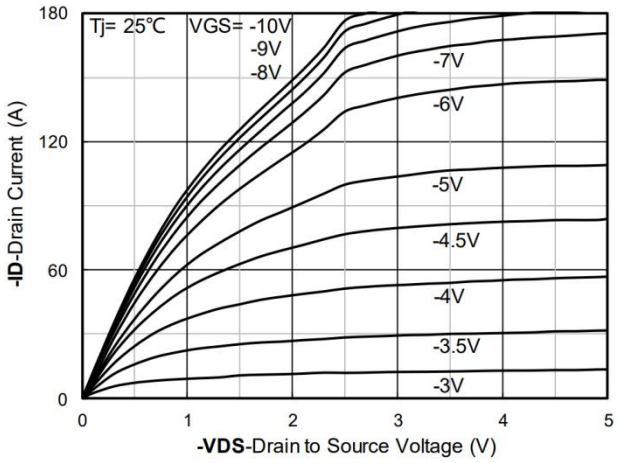


Figure 1. Output Characteristics

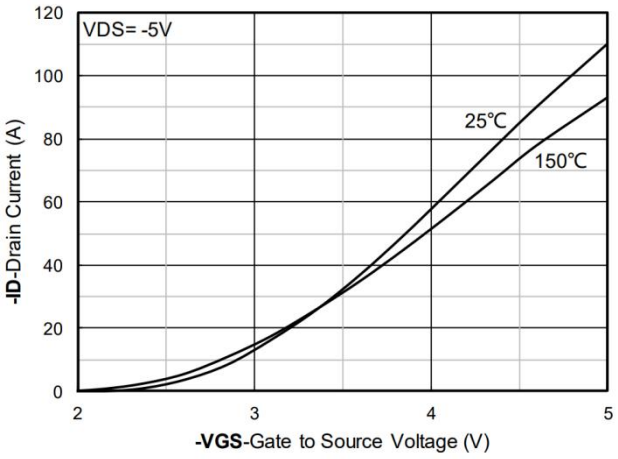


Figure 2. Transfer Characteristics

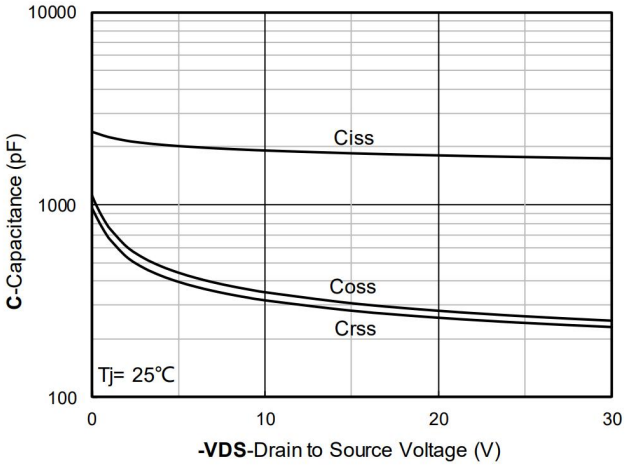


Figure 3. Capacitance Characteristics

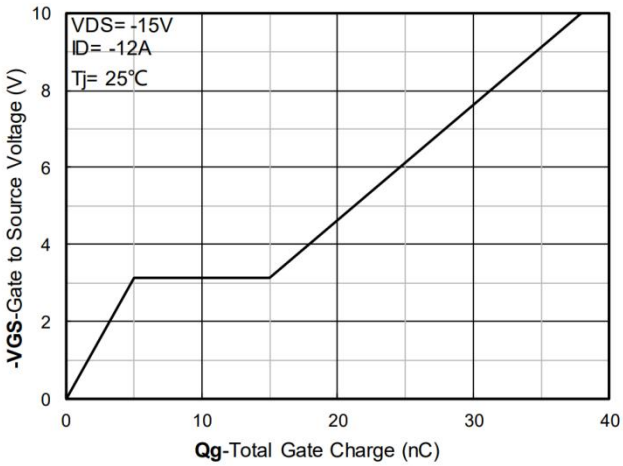


Figure 4. Gate Charge

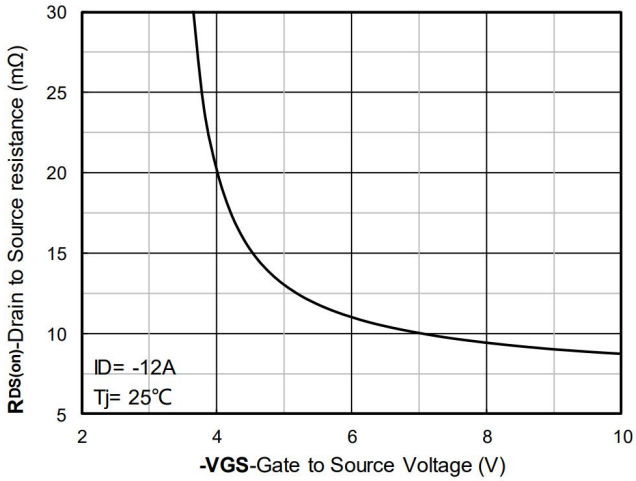


Figure 5. On-Resistance vs Gate to Source Voltage

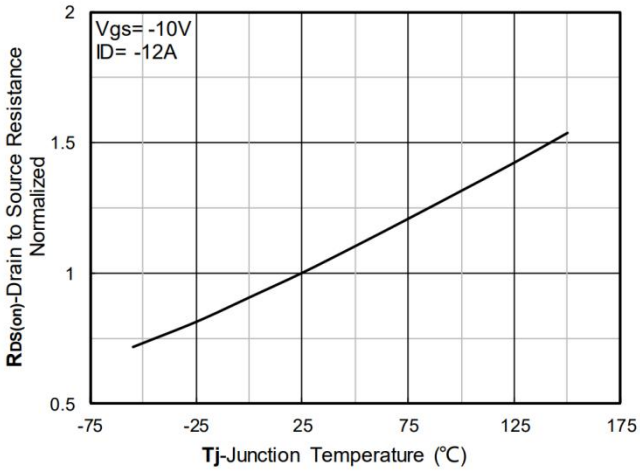


Figure 6. Normalized On-Resistance

Typical Characteristics

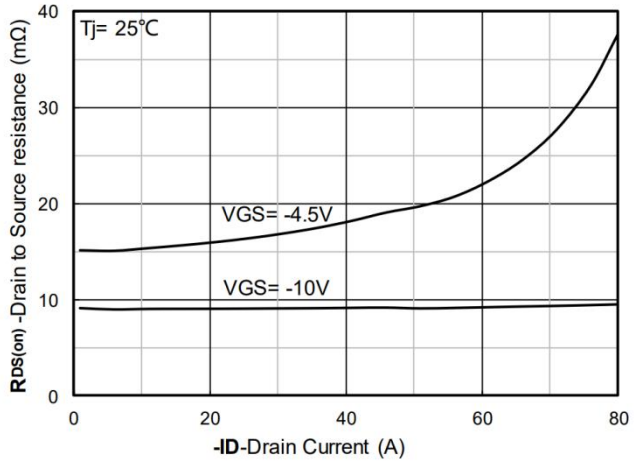


Figure 7. RDS(on) VS Drain Current

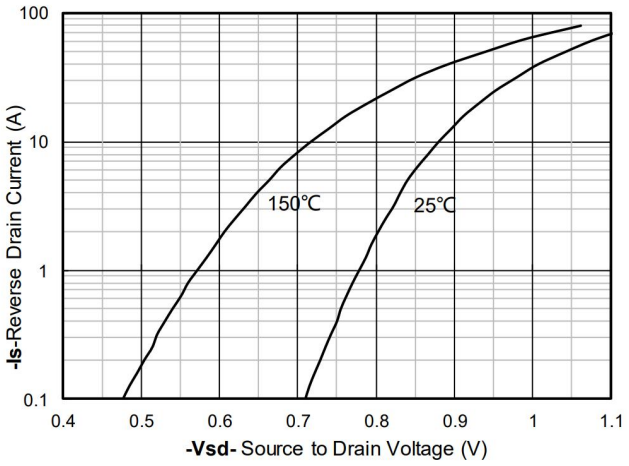


Figure 8. Forward characteristics of reverse diode

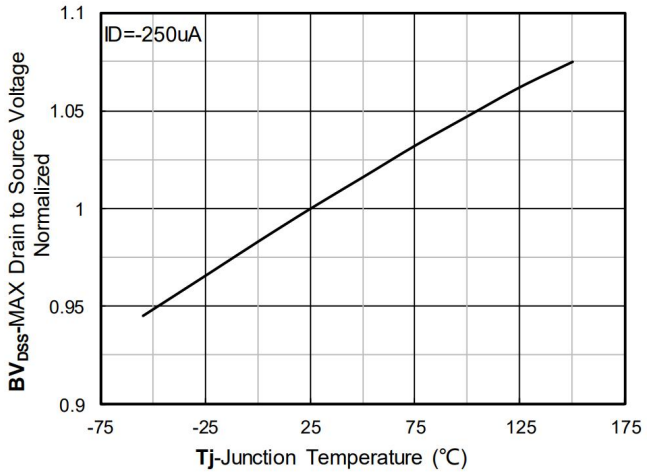


Figure 9. Normalized breakdown voltage

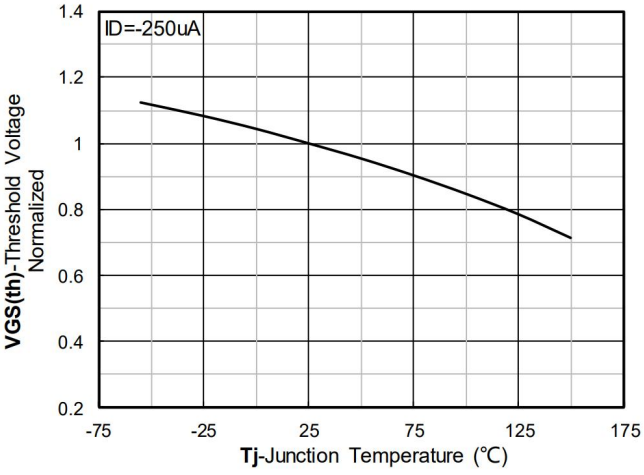


Figure 10. Normalized Threshold voltage

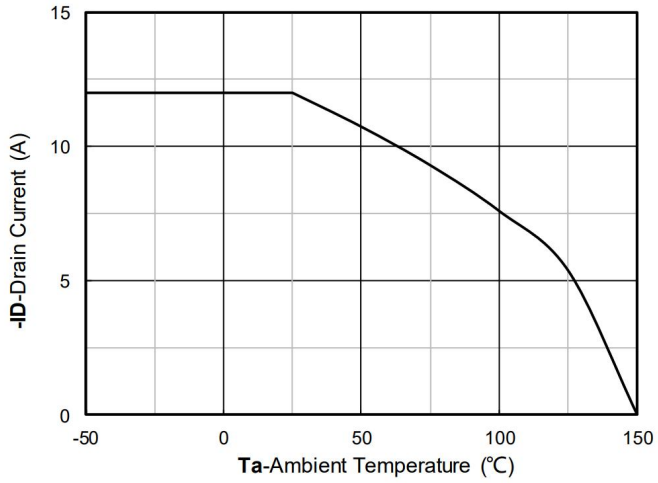


Figure 11. Current dissipation

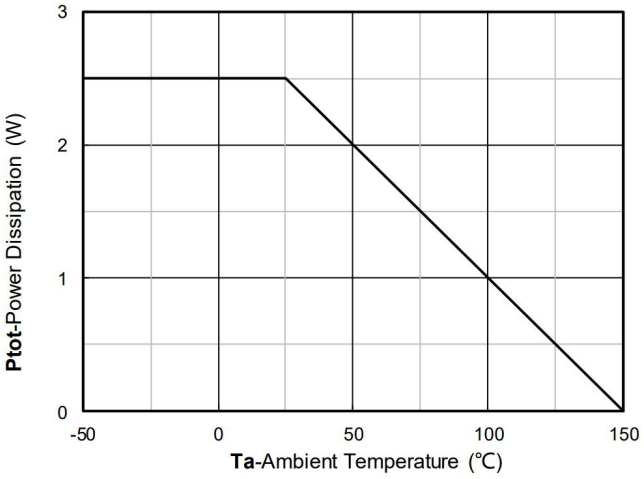


Figure 12. Power dissipation

Typical Characteristics

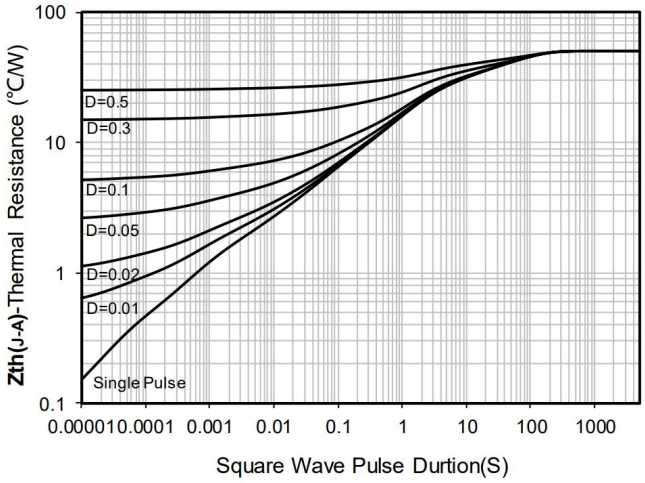


Figure 13. Maximum Transient Thermal Impedance

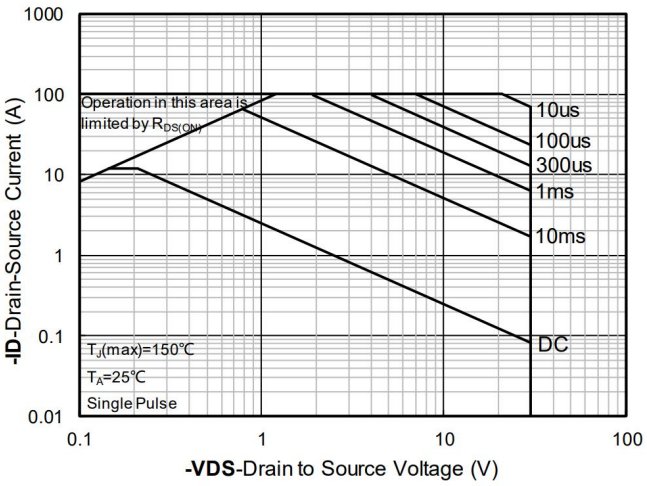
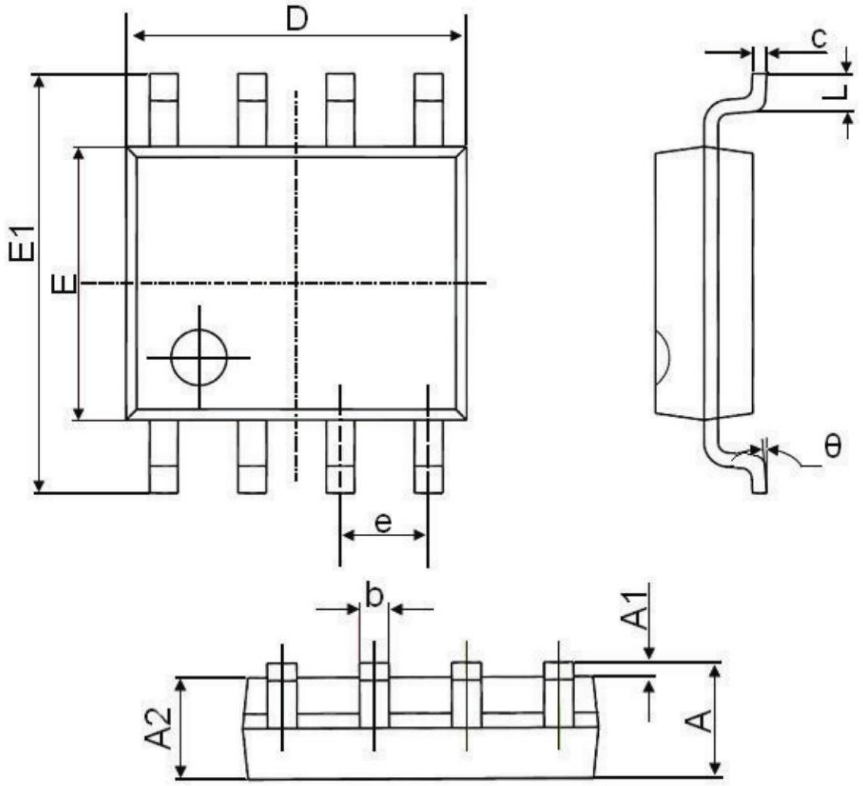


Figure 14. Safe Operation Area

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.250	1.650	0.049	0.065
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°